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Measurements on last IMB-CNM LGADs production

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In this contribution we will present measurements on LGADs corresponding to our CNM's second production run based on 6-inch, 50 μ m active layer thick, Si-Si wafers (6LG2-v2 technology). The wafers were carbon enriched using five different implantation doses and one implantation energy. For the gain layer, samples were fabricated using a single boron implantation dose and energy. Measurements and analysis of the electrical characterization and radiation hardness were carried out on these LGADs.

Author: Mr VILLEGAS DOMINGUEZ, Jairo Antonio (IMB-CNM (CSIC))

Co-authors: Dr PELLEGRINI, Giulio (IMB-CNM (CSIC)); Mr MANOJLOVIC, Milos (IMB-CNM (CSIC)); Dr MOFFAT, Neil (IMB-CNM (CSIC)); Dr HIDALGO VILLENA, Salvador (IMB-CNM (CSIC))

Presenter: Mr VILLEGAS DOMINGUEZ, Jairo Antonio (IMB-CNM (CSIC))

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